

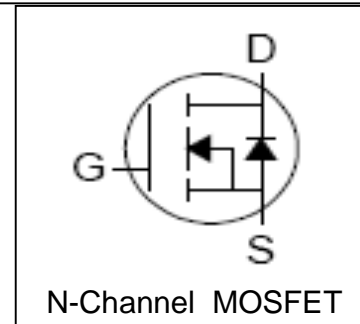
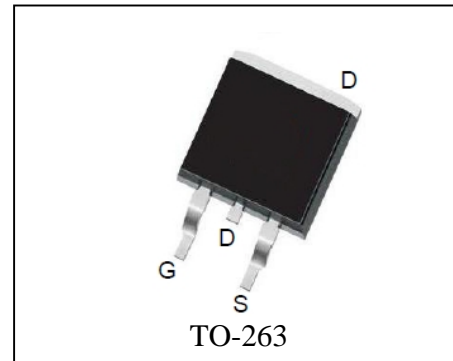
Features

- 40V/120A,
R_{DS(ON)} = 2.7mΩ (Typ.) @ V_{GS} = 10V
- Ultra Low On-Resistance
- Fast Switching
- 100% avalanche tested
- 175°C Operating Temperature
- Lead Free, RoHS compliant

Applications

- Switching Application Systems
- UPS

Pin Description



Absolute Maximum Ratings

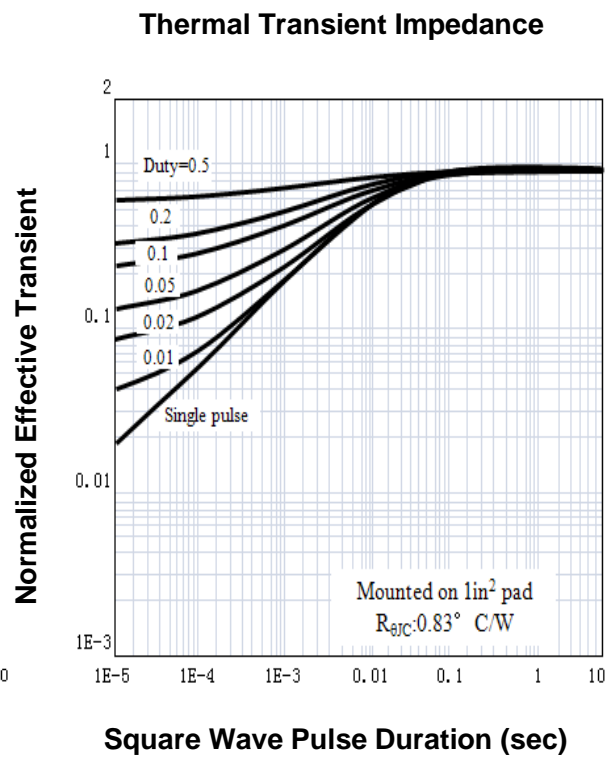
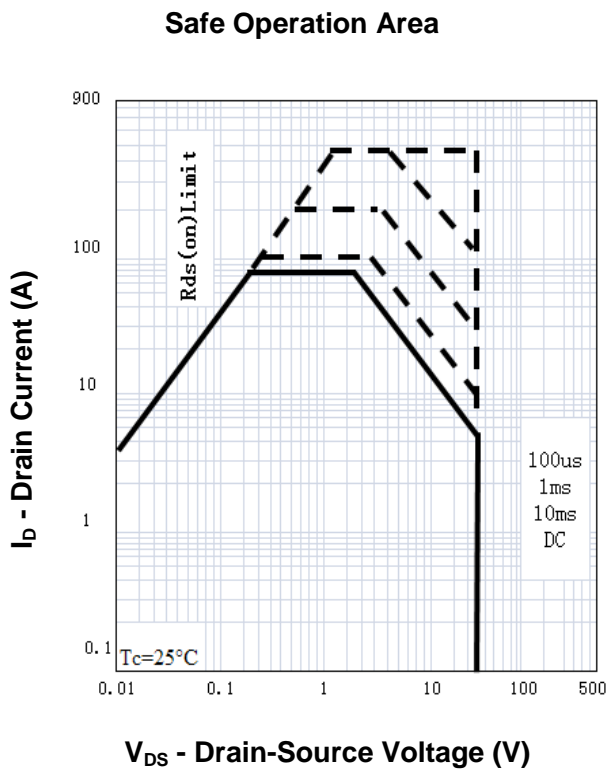
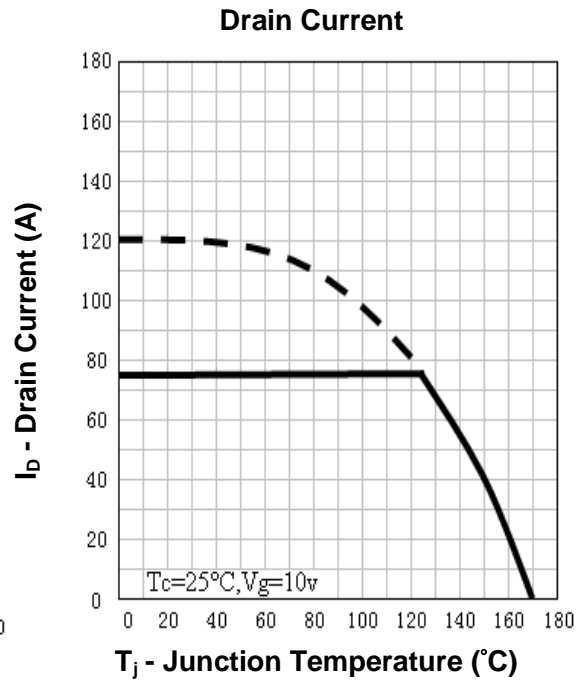
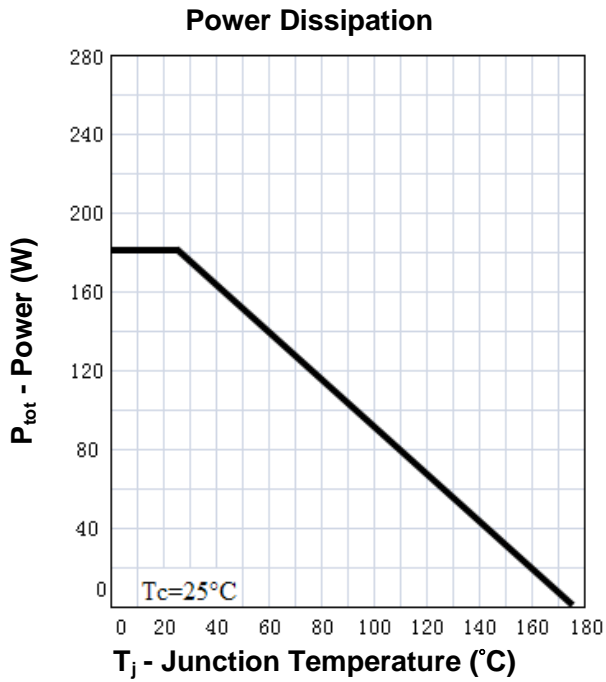
Symbol	Parameter	Rating	Unit
Common Ratings (T _A = 25°C Unless Otherwise Noted)			
V _{DSS}	Drain-Source Voltage	40	V
V _{GSS}	Gate-Source Voltage	±20	
T _J	Maximum Junction Temperature	175	°C
T _{STG}	Storage Temperature Range	-55 to 175	°C
I _S	Diode Continuous Forward Current	T _C = 25°C 120 ^①	A
Mounted on Large Heat Sink			
I _{DP}	300µs Pulse Drain Current Tested	T _C = 25°C 480 ^②	A
I _D	Continuous Drain Current (V _{GS} = 10V)	T _C = 25°C 120 ^①	A
		T _C = 100°C 100 ^①	
P _D	Maximum Power Dissipation	T _C = 25°C 180	W
		T _C = 100°C 90	
R _{θJC}	Thermal Resistance-Junction to Case	0.83	°C/W
Drain-Source Avalanche Ratings			
E _{AS} ^③	Avalanche Energy, Single Pulsed	1260	mJ

Electrical Characteristics ($T_A=25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	RU35122S			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	40			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=40V, V_{GS}=0V$ $T_J=85^\circ\text{C}$			1 30	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	2	3	4	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
$R_{DS(ON)}$ ^④	Drain-Source On-state Resistance	$V_{GS}=10V, I_{DS}=60A$		2.7	3.7	m Ω
Diode Characteristics						
V_{SD} ^④	Diode Forward Voltage	$I_{SD}=60A, V_{GS}=0V$			1.2	V
t_{rr}	Reverse Recovery Time	$I_{SD}=60A, di_{SD}/dt=100A/\mu s$		26		ns
Q_{rr}	Reverse Recovery Charge			32		nC
Dynamic Characteristics ^⑤						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$		1.4		Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=32V,$ Frequency=1.0MHz		4220		pF
C_{oss}	Output Capacitance			970		
C_{riss}	Reverse Transfer Capacitance			520		
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=20V, R_L=35\Omega,$ $I_{DS}=60A, V_{GEN}=10V,$ $R_G=4\Omega$		17		ns
t_r	Turn-on Rise Time			105		
$t_{d(OFF)}$	Turn-off Delay Time			35		
t_f	Turn-off Fall Time			30		
Gate Charge Characteristics ^⑤						
Q_g	Total Gate Charge	$V_{DS}=32V, V_{GS}=10V,$ $I_{DS}=60A$		95		nC
Q_{gs}	Gate-Source Charge			17		
Q_{gd}	Gate-Drain Charge			38		

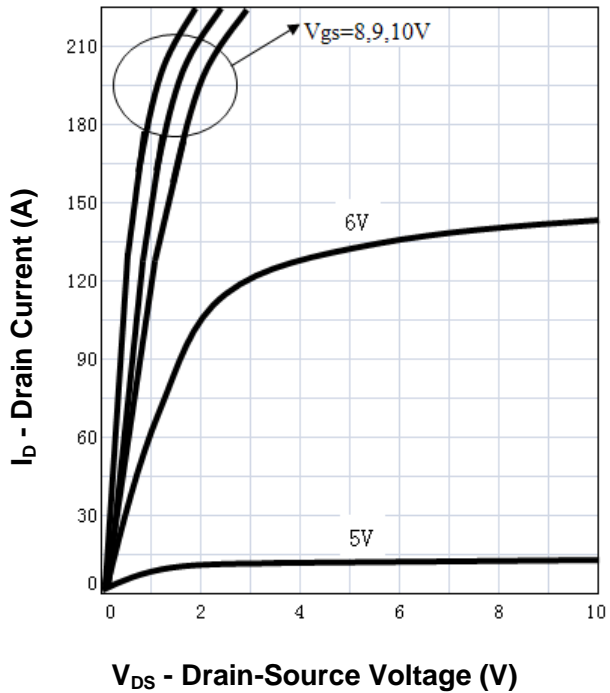
- Notes: ① Calculated continuous current based on maximum allowable junction temperature. Current limited by bond wire. Package limitation current is 75A.
 ② Pulse width limited by safe operating area.
 ③ Limited by $T_{Jmax}, I_{AS}=71A, V_{DD}=48V, R_G=47\Omega$, Starting $T_J=25^\circ\text{C}$.
 ④ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 ⑤ Guaranteed by design, not subject to production testing.

Typical Characteristics

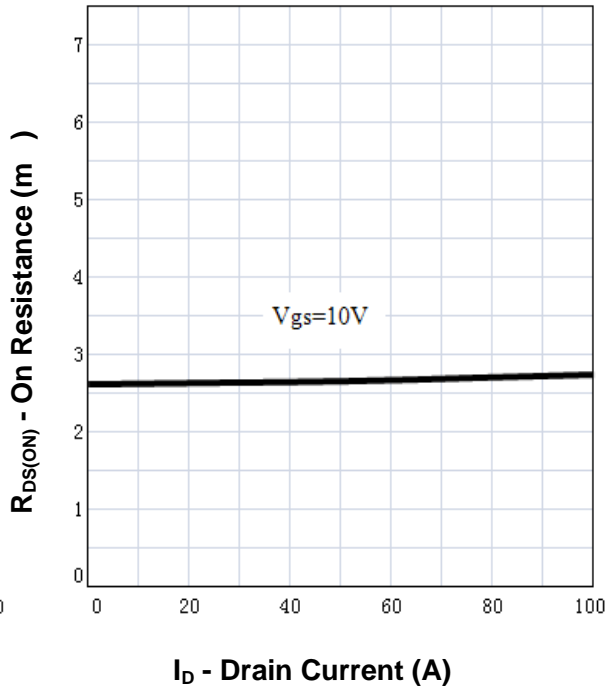


Typical Characteristics

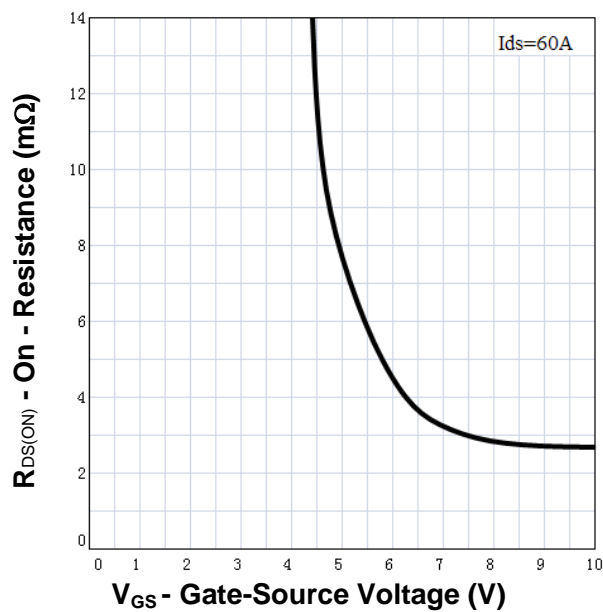
Output Characteristics



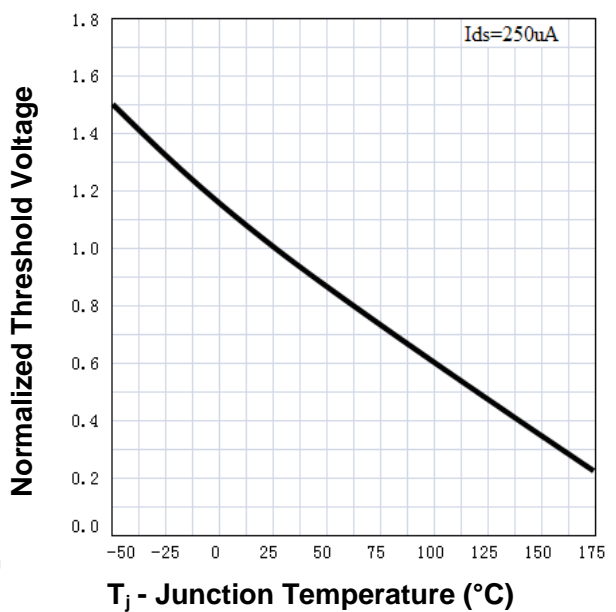
Drain-Source On Resistance



Drain-Source On Resistance

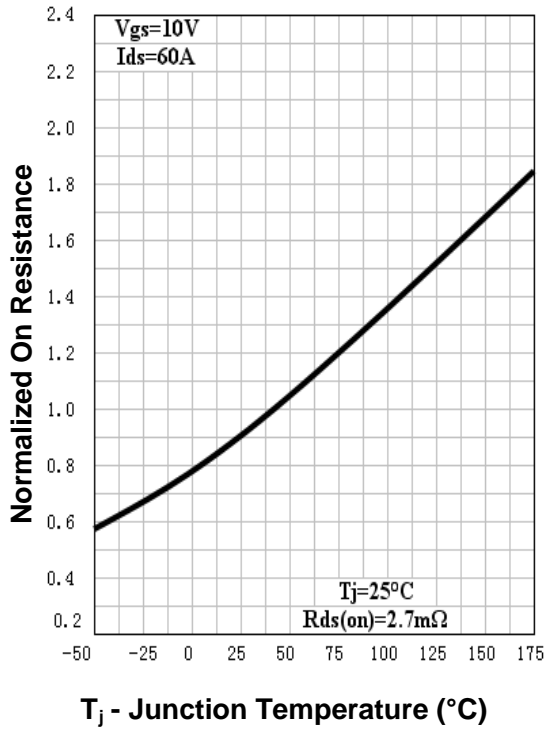


Gate Threshold Voltage

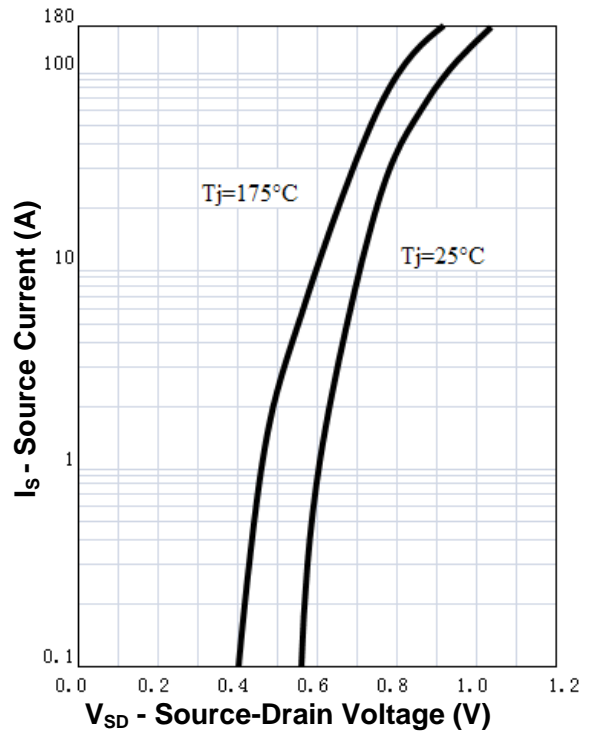


Typical Characteristics

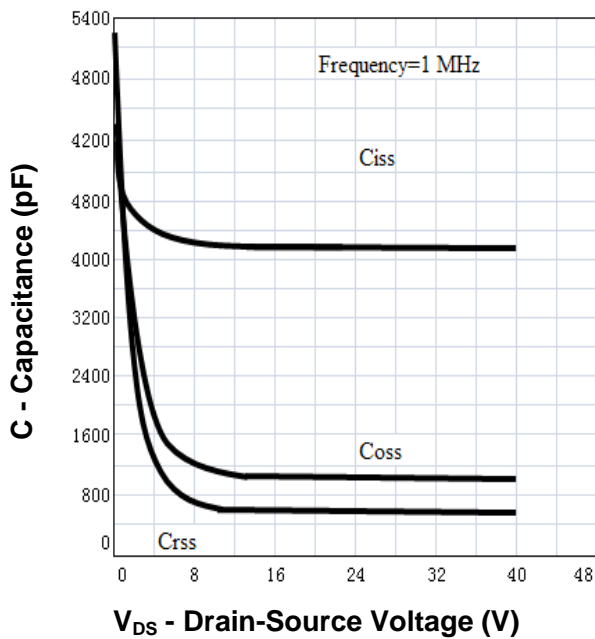
Drain-Source On Resistance



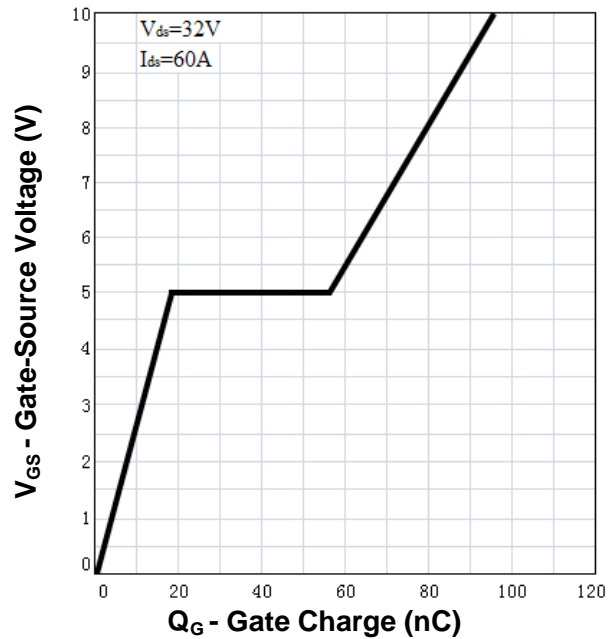
Source-Drain Diode Forward



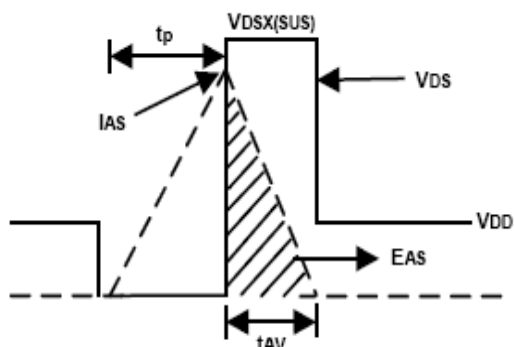
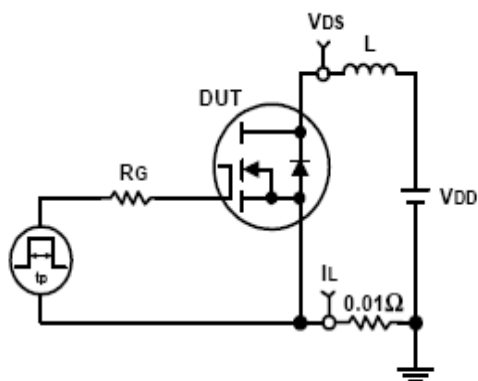
Capacitance



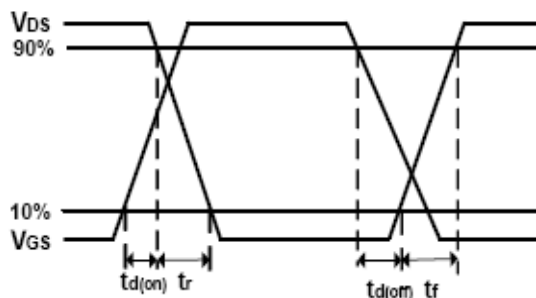
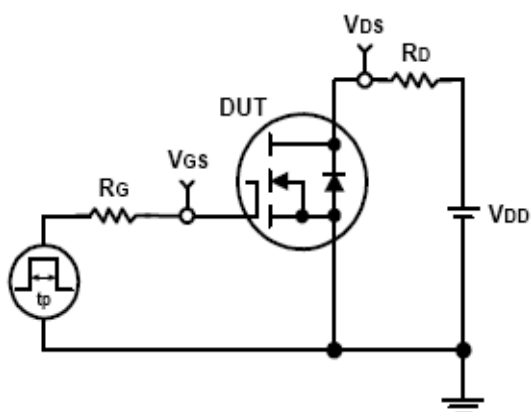
Gate Charge



Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms

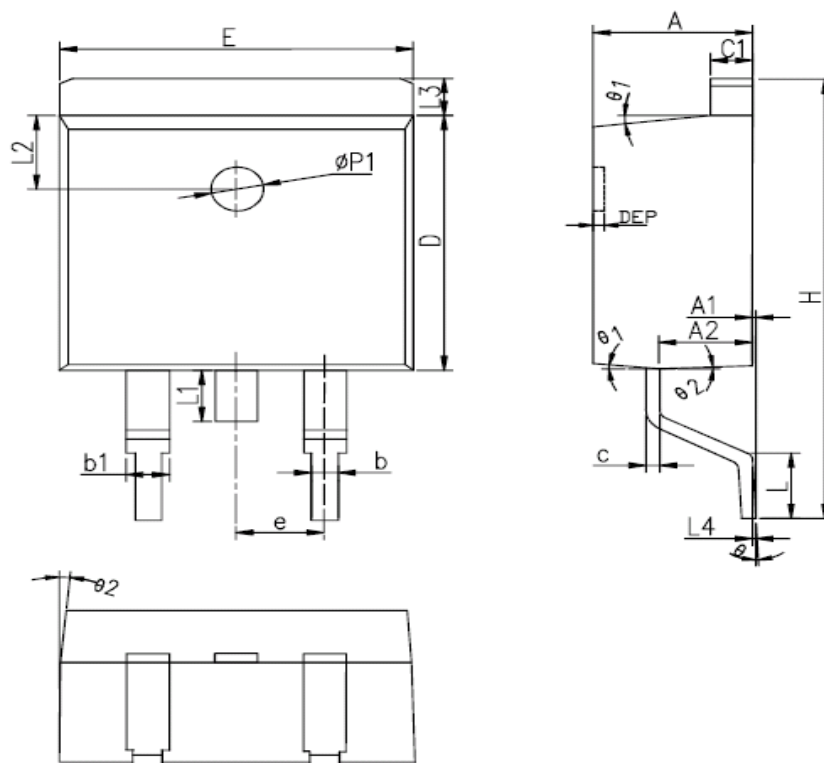


Ordering and Marking Information

Device	Marking	Package	Packaging	Quantity	Reel Size	Tape width
RU35122S	RU35122S	TO-263	Tube	50	-	-

Package Information

TO-263-2L



SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185	L	2.00	2.30	2.60	0.079	0.090	0.102
A1	0	0.10	0.25	0	0.004	0.010	L3	1.17	1.27	1.40	0.046	0.050	0.055
A2	2.59	2.69	2.79	0.102	0.106	0.110	L1	-	-	1.70	-	-	0.067
b	0.77	-	0.90	0.030	-	0.035	L4	0.25BSC			0.01BSC		
b1	1.23	-	1.36	0.048	-	0.052	L2	2.50REF.			0.098REF.		
c	0.34	-	0.47	0.013	-	0.019	θ	0°	-	8°	0°	-	8°
C1	1.22	-	1.32	0.048	-	0.052	θ 1	5°	7°	9°	5°	7°	9°
D	8.60	8.70	8.80	0.338	0.343	0.346	θ 2	1°	3°	5°	1°	3°	5°
E	10.00	10.16	10.26	0.394	0.4	0.404	DEP	0.05	0.10	0.20	0.002	0.004	0.008
e	2.54BSC			0.1BSC			Øp1	1.40	1.50	1.60	0.055	0.059	0.063
H	14.70	15.10	15.50	0.579	0.594	0.610							

ALL DIMENSIONS REFER TO JEDEC STANDARD
DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS

Customer Service

Worldwide Sales and Service:

Sales@ruichips.com

Technical Support:

Technical@ruichips.com

Investor Relations Contacts:

Investor@ruichips.com

Marcom Contact:

Marcom@ruichips.com

Editorial Contact:

Editorial@ruichips.com

HR Contact:

HR@ruichips.com

Legal Contact:

Legal@ruichips.com

Shen Zhen RUICHIPS Semiconductor CO., LTDRoom 501, the 5floor An Tong Industrial Building,
NO.207 Mei Hua Road Fu Tian Area Shen Zhen City, CHINA**TEL:** (86-755) 8311-5334**FAX:** (86-755) 8311-4278**E-mail:** Sales-SZ@ruichips.com